

116 Amendment
09/728,193 (09792909-4714)
Page 2

OK to
enter
MS
6/21/04

IN THE CLAIMS

1. (Previously presented) A method of manufacturing a crystal of a III-V compound of a nitride system, the method comprising:

growing a crystal of a III-V compound of the nitride system having a predetermined thickness on a surface of a basal body,

wherein the growth step comprises:

forming a first plurality of patterns of at least one pitch, in one position in a direction of a thickness of the crystal; and

forming a second plurality of patterns of at least one pitch, in another position in the direction of the thickness of the crystal;

wherein the second plurality of patterns at least partly overlies said first plurality of patterns in the direction of the thickness of the crystal and at least partly does not overlie said first plurality of patterns in the direction of the thickness of the crystal; and

wherein said at least one pitch of pattern elements of said first plurality of patterns and said at least one pitch of pattern elements of said second plurality of patterns are different from each other.

2. (Previously presented) A method of manufacturing a crystal of a III-V compound of a nitride system as claimed in claim 1,

wherein each of the first and second plurality of patterns takes form in pattern elements arranged in one direction in a plane almost parallel to the surface of the basal body.

3. (Canceled)

4. (Previously presented) A method of manufacturing a crystal of a III-V compound of a nitride system as claimed in claim 2,